

# **Production of Quasi-Monochromatic GeV Photons by Compton Scattering using Undulator X-ray Radiation at SPring-8**

**H. Ohkuma, A. Mochihashi , M. Oishi, S. Suzuki, K. Tamura,  
T. Nakano<sup>(1)</sup>, H. Shimizu<sup>(2)</sup>**

**JASRI/SPring-8, <sup>(1)</sup>Osaka Univ., <sup>(2)</sup>Tohoku Univ.**

**This work is supported by the Japan Society for the Promotion of Science  
under the Grant-and-Aid for Scientific Research (Contract no. 24241035)**

# Outline

- **Motivation**
- **LEPS2 Activity at SPring-8**
- **Theory of Backward Compton Scattering of Quasi-Monochromatic  $\gamma$ -ray**
- **Preliminary Reflectivity Measurements of Single Crystal**
- **Plan of Test Experiment for  $\gamma$ -ray Production**
- **Summary**

# Motivation

- **BCS using laser (infrared to ultra-violet) established with successful results, but extension of the maximum photon energy of  $\gamma$ -ray opens new fields of the photo production experiments of nuclear and particle physics**



**LEP and LEP2(BL31LEP) at SPring-8**

- **Quasi-monochromatic  $\gamma$ -ray**



**No tagging system ( $\gamma$  -ray intensity and energy are measured)**

- **In SR facility, many high power X-ray undulators. Very attractive to use as incident photon source for BCS**



**Photon energy close to the kinematic limit**

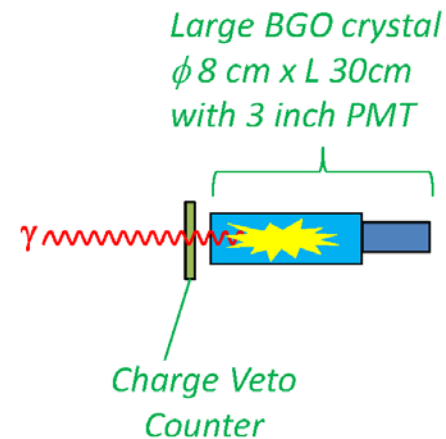
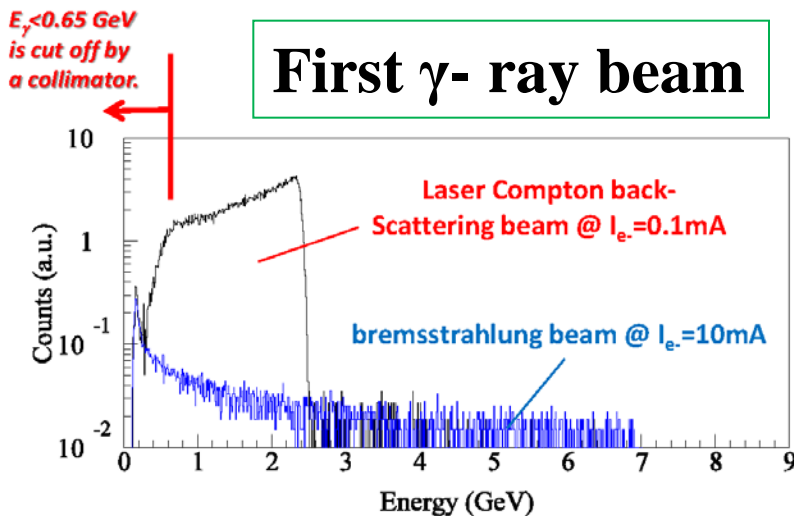
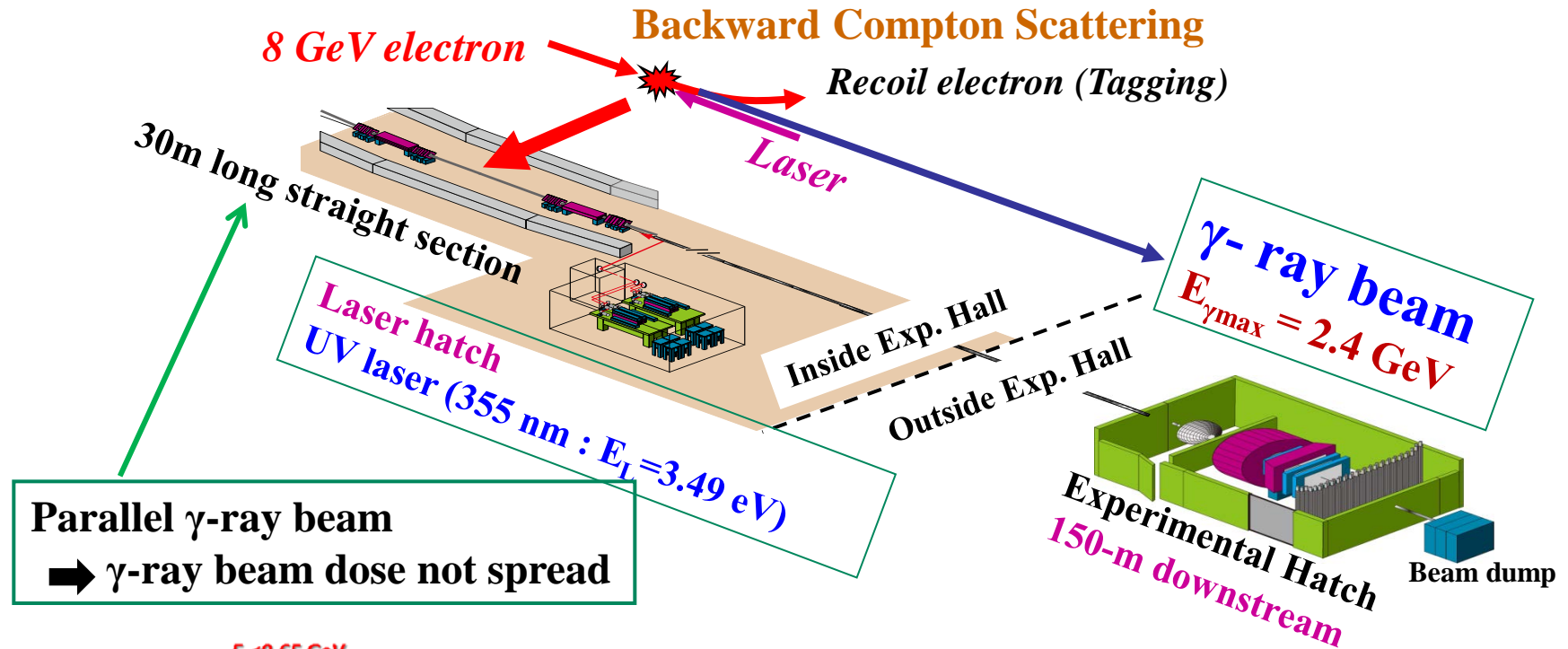
- **Single crystal with high-reflectivity at normal-incidence (K-J. Kim et al.)**



**X-ray photon reflected back by a single crystal**

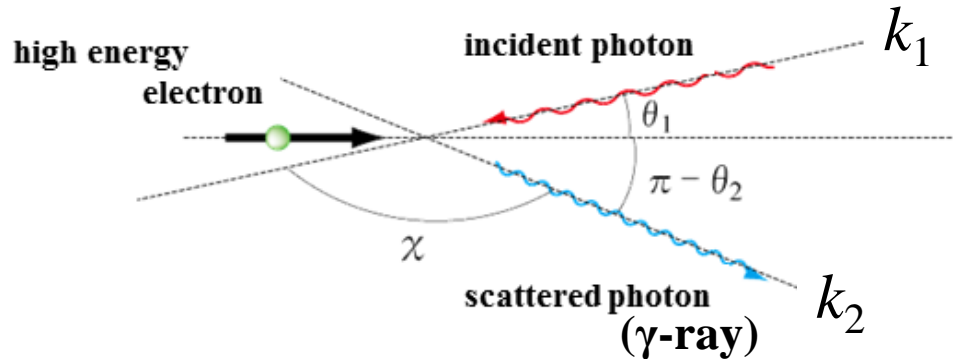
- **Low energy operation in future SPring-8**

# BL31LEP constructed at long straight section of SPring-8



# Theory of Backward Compton Scattering

## Schematic diagram of BCS



$$k_2 = k_1 \frac{1 + \beta \cos \theta_1}{1 + \beta \cos \theta_2 + \frac{k_1}{E_e} (1 - \cos \chi)} \quad (1)$$

In case of head-on collision, maximum energy of scattered Photon :

$$k_{2\max} = \frac{k_1(1 + \beta)}{1 + \beta + \frac{2k_1}{E_e}} \approx \frac{4k_1 E_e^2}{(m_e c^2)^2 + 4k_1 E_e} \quad (2)$$

When  $k_1$  is 10 keV,  $E_e = 8$  GeV  $\Rightarrow k_{2\max} \sim 8$  GeV

(photon energy of  $\gamma$ -ray is almost equal to electron energy).

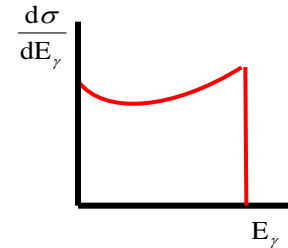
## Spectrum shape (Milburn, 1963)

$$\frac{1}{\sigma_0} \frac{d\sigma}{d(k_2/E_e)} = \frac{3}{16\lambda} \left[ \frac{\lambda^2(1-x)^2}{1+\lambda(1-x)} + 2(1+x^2) + O[x^n] \right] \quad (3)$$

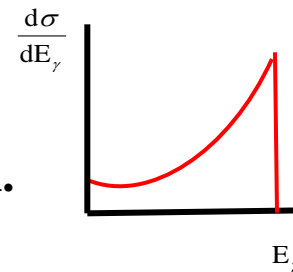
$\sigma_0$  : Thomson scattering cross-section,

$\lambda = 2\gamma k_1/m_e c^2$ ,  $x = \cos\theta_0$  ( $\theta_0$  : photon scattering angle)

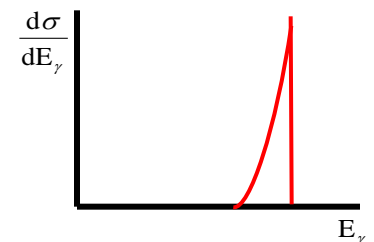
For small  $k_1$  (e. g. laser light,  $E_1 = 3.49$  eV),  
the second term of Eq. (3) is dominant.  
 $\gamma$ -ray spectrum is the parabolic shape  
with wide photon energy range.

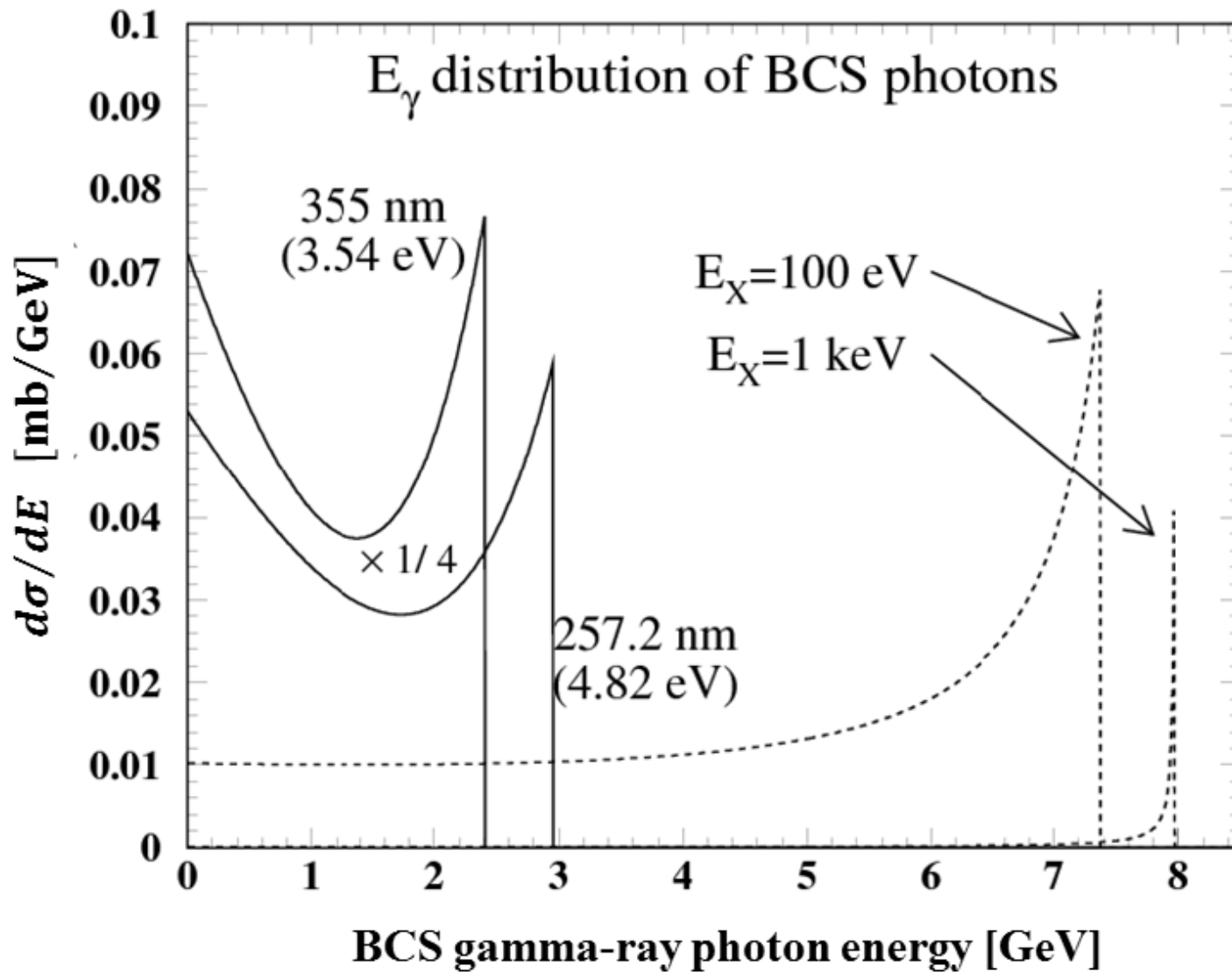


For large  $k_1$  (e. g. undulator,  $E_1 > 100$  eV ),  
the first term is dominant and  
 $\gamma$ -ray spectrum damps in the low energy region.

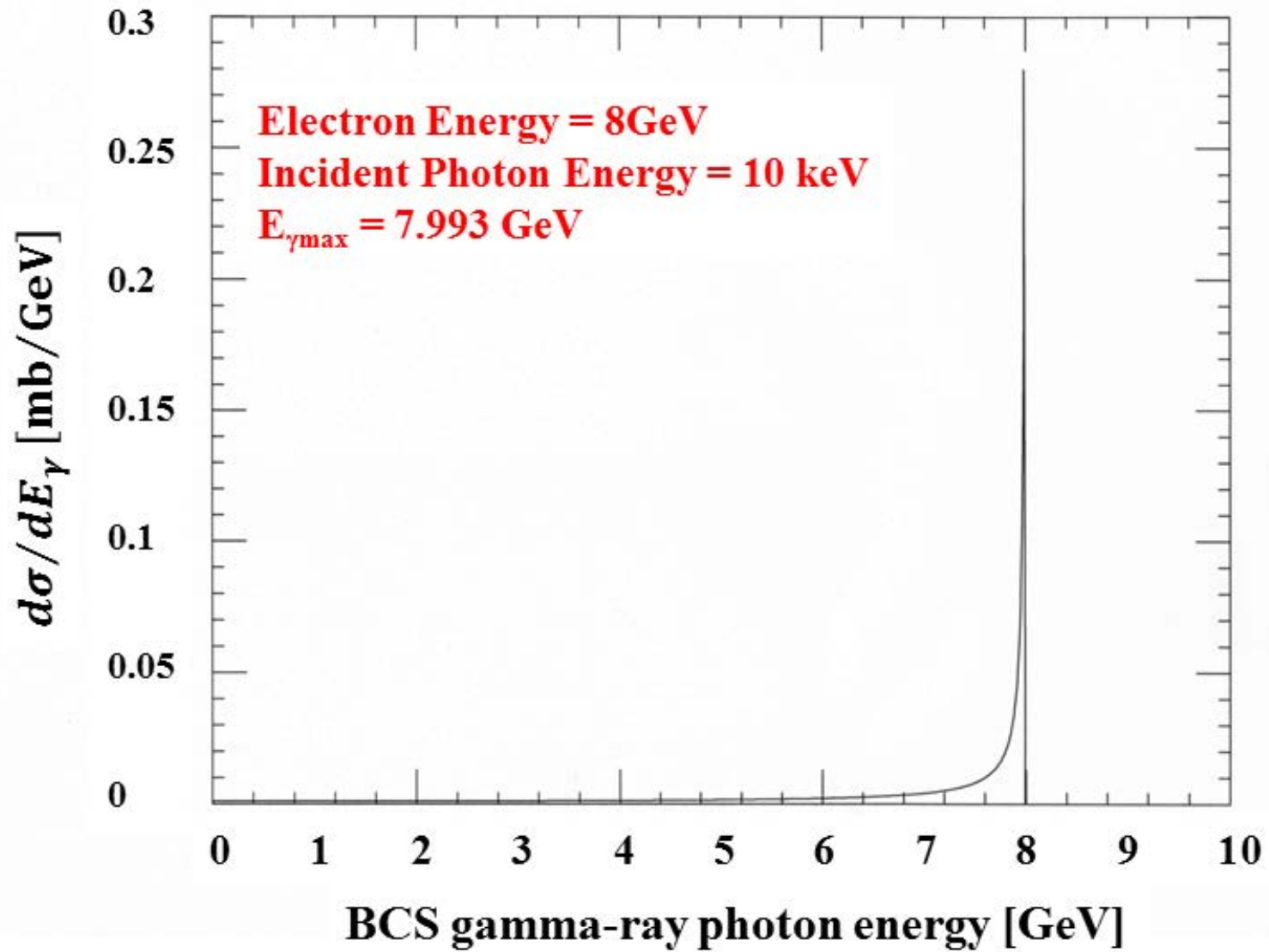


For very large  $k_1$  (e. g. hard X-ray undulator,  $E_1 > 5\text{keV}$  ),  
higher-order term  $x^n$  ( $n > 2$ ) of Eq. (3) becomes important.  
 $\gamma$ -ray spectrum uprises steeply near the maximum BCS gamma-ray of  $k_{2\text{max}}$ .





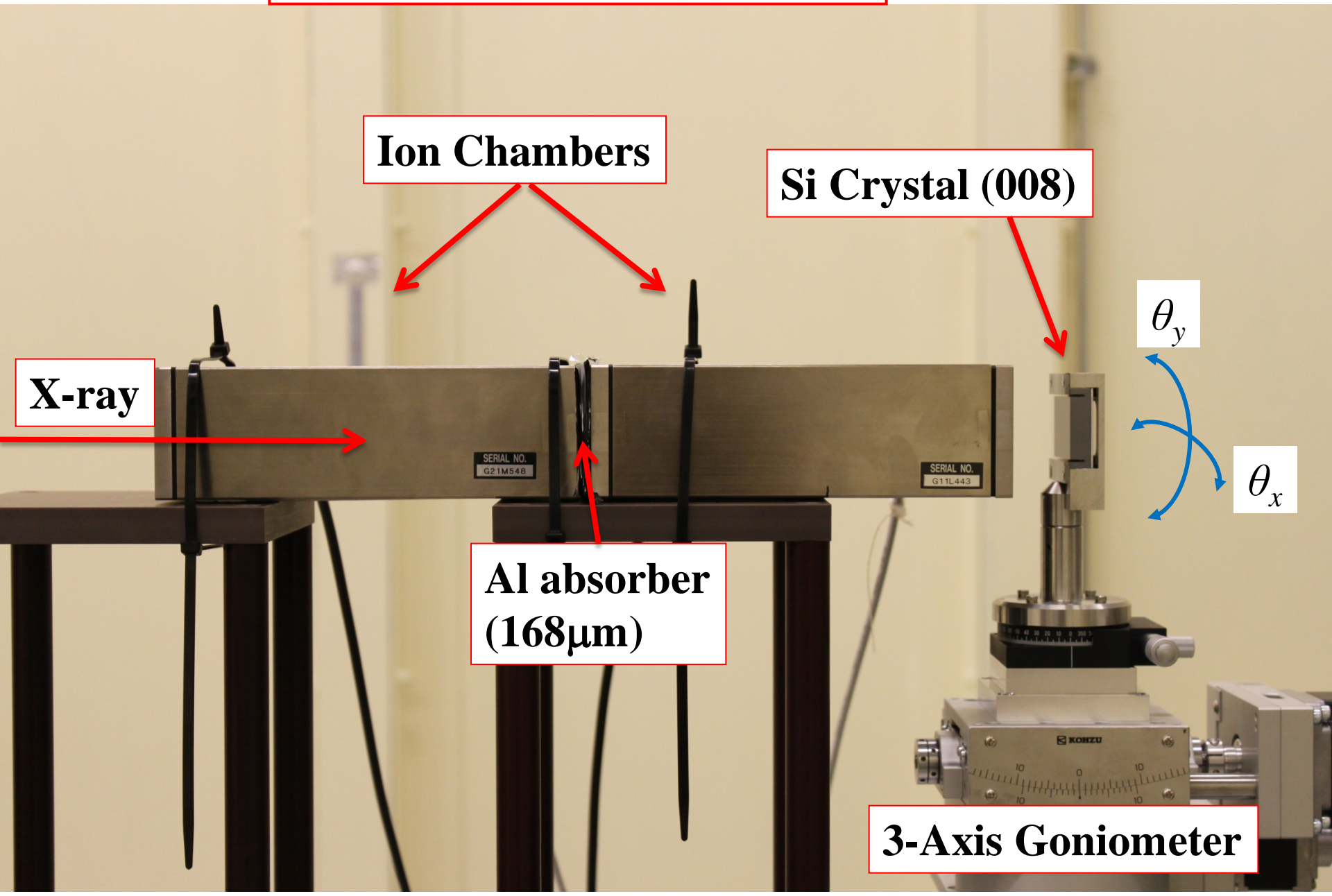
Calculated  $\gamma$ -ray distribution as a parameter of incident photon energy



**10keV incident X-ray and Produced  $\gamma$ -ray in kinematic limit**



# Reflectivity Measurement



X-ray

Ion Chambers

Si Crystal (008)

$\theta_y$

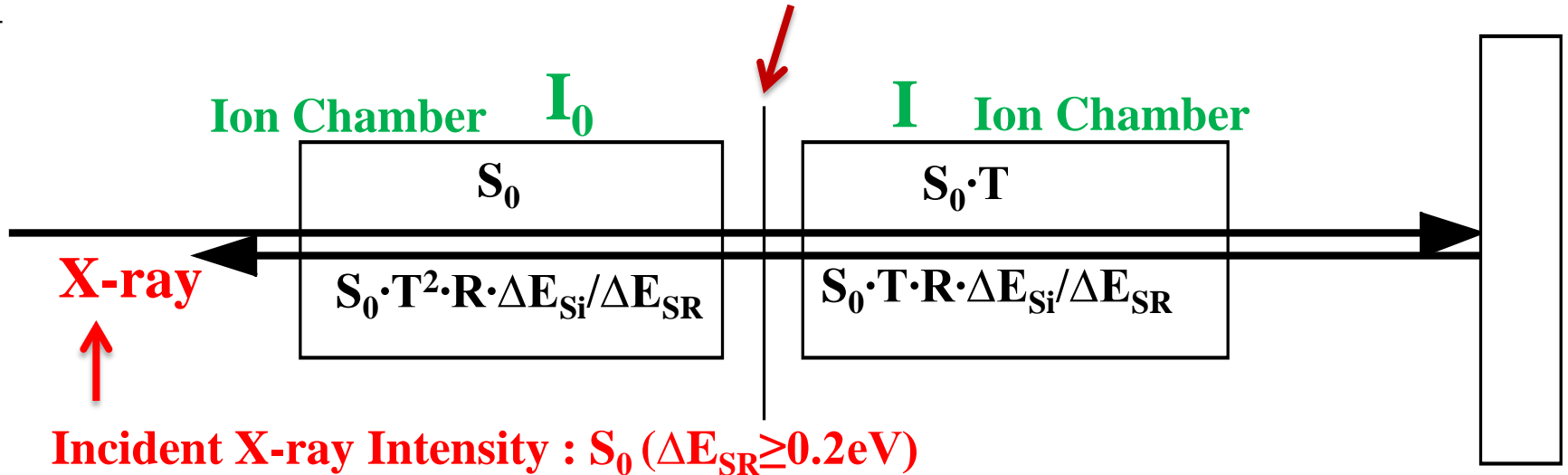
$\theta_x$

Al absorber  
(168 $\mu\text{m}$ )

3-Axis Goniometer

**Al absorber (Thickness = 168 $\mu$ m) : T~0.23**

**Si Mirror**



$$\frac{I}{I_0} = C \cdot \frac{S_0 \cdot T + S_0 \cdot T \cdot R \cdot \frac{\Delta E_{Si}}{\Delta E_{SR}}}{S_0 + S_0 \cdot T^2 \cdot R \cdot \frac{\Delta E_{Si}}{\Delta E_{SR}}} = C \cdot T \left( 1 + R \cdot \frac{\Delta E_{Si}}{\Delta E_{SR}} \right) = 0.23C(1 + 0.3R)$$

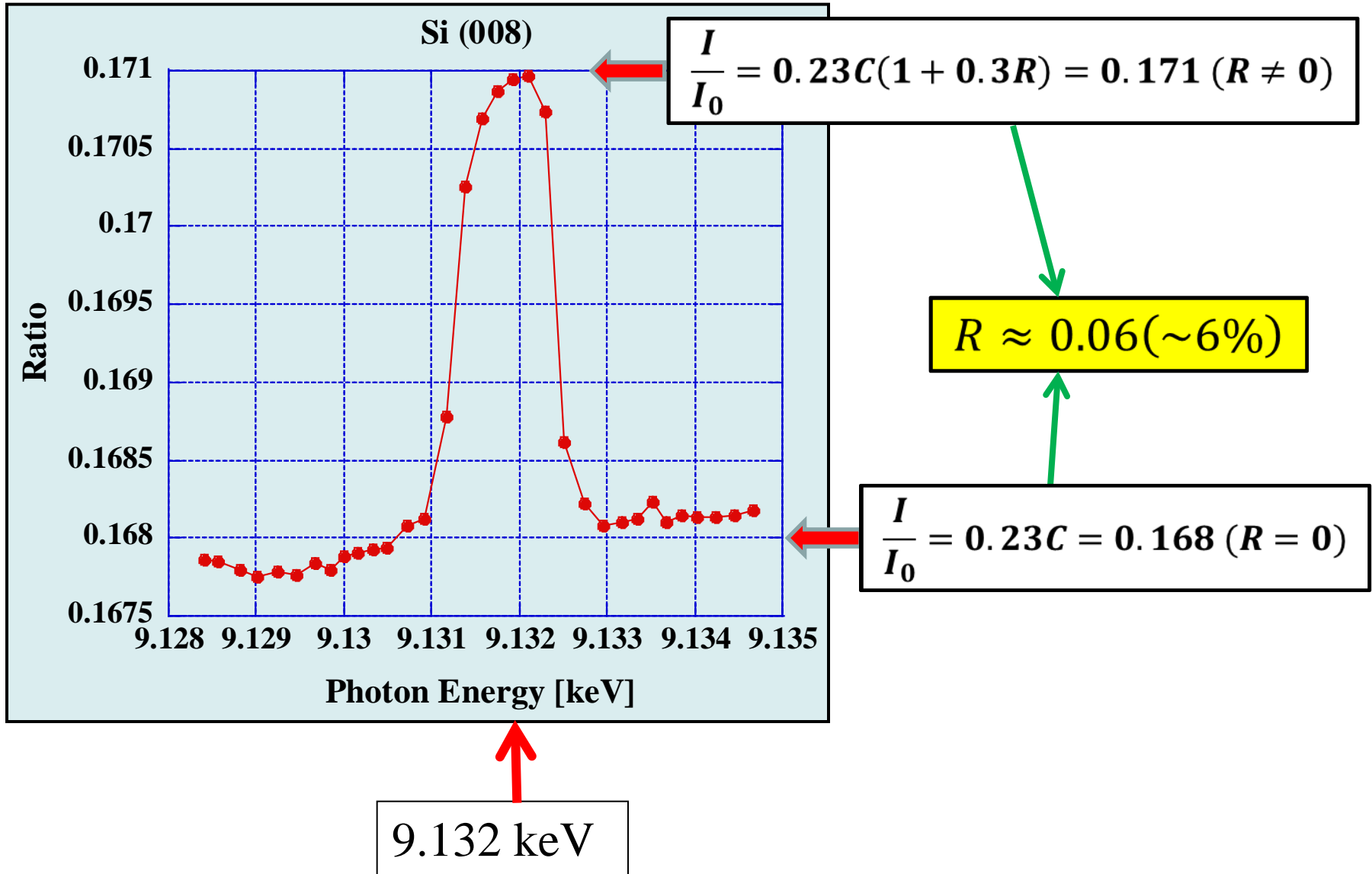
$$\frac{I}{I_0} = 0.23C = 0.168 \quad (R=0)$$

$$\frac{I}{I_0} = 0.23C(1 + 0.3R) = 0.171 \quad (R \neq 0)$$

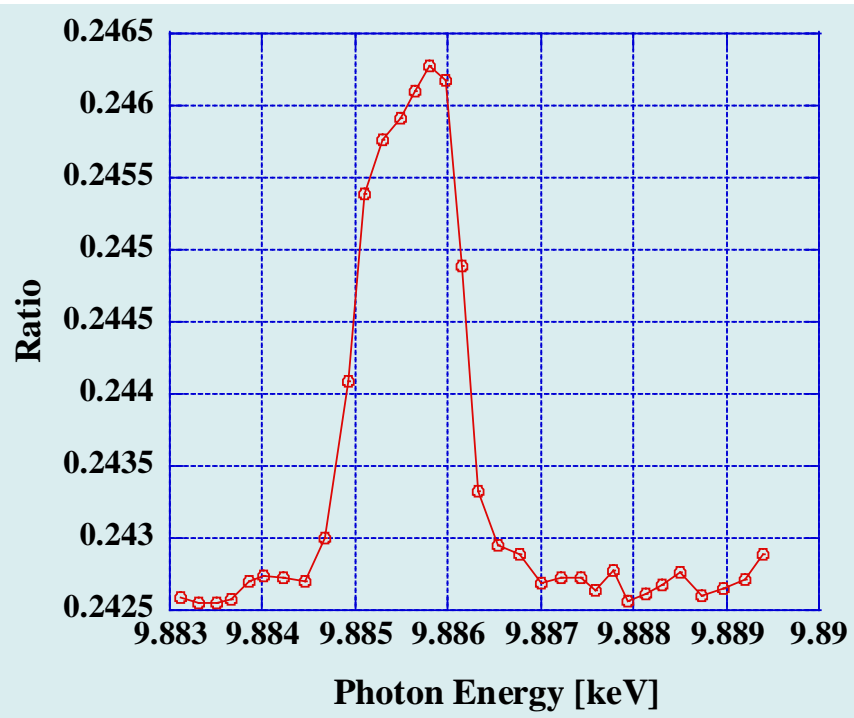
$$\boxed{R \approx 0.06 \text{ (~6\%)}}$$

cf. Si (333)  $R \approx 0.11$  (~11%)、Si (555)  $R \approx 0.05$  (~5%)

# Si (008) Bragg Reflection at normal-incidence



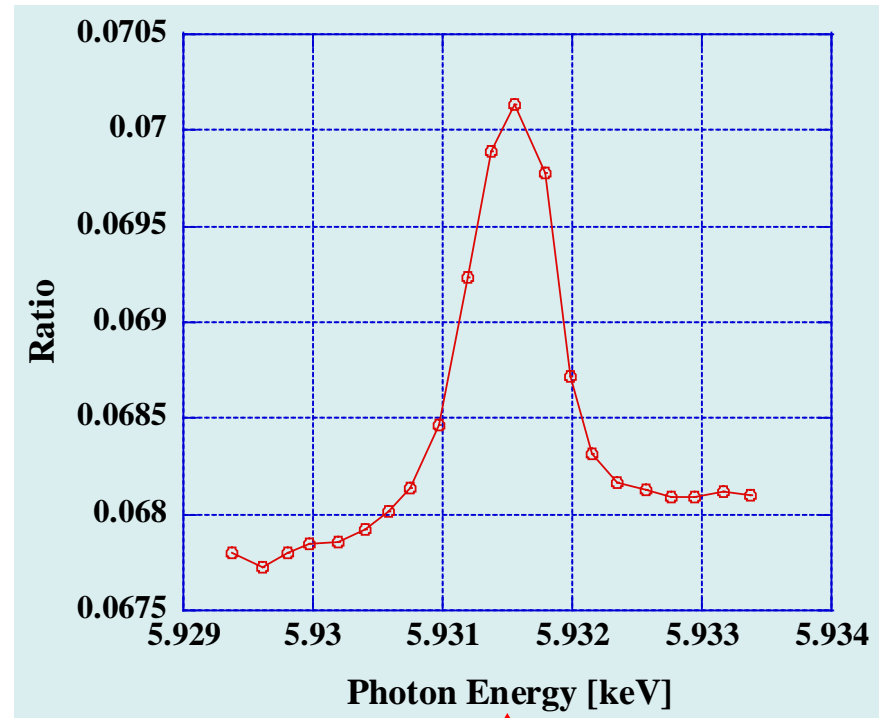
Si (5 5 5)



9.886 keV

Si (555)  $R \approx 0.05$  (~5%)

Si (3 3 3)

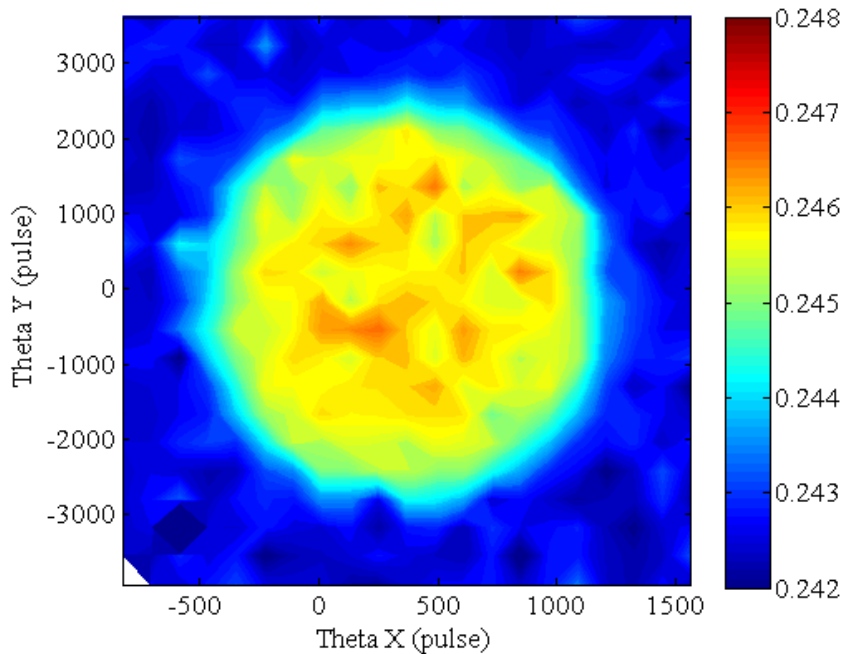


5.9315 keV

Si (333)  $R \approx 0.11$  (~11%)

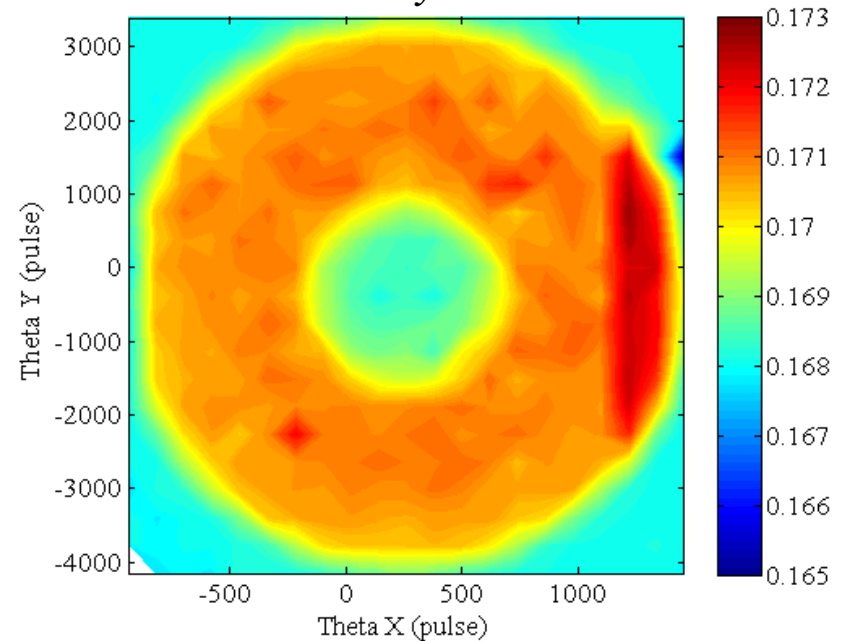
# Scanning Pattern of ion-chamber output signal (I) by 2-axis ( $\theta_x$ and $\theta_y$ ) scanning

$\theta_x$  and  $\theta_y : \pm 1.5$



$\theta_x - \theta_y$  scan @ normal-incidence  
of **9.132 keV**

$\theta_x$  and  $\theta_y : \pm 1.5$

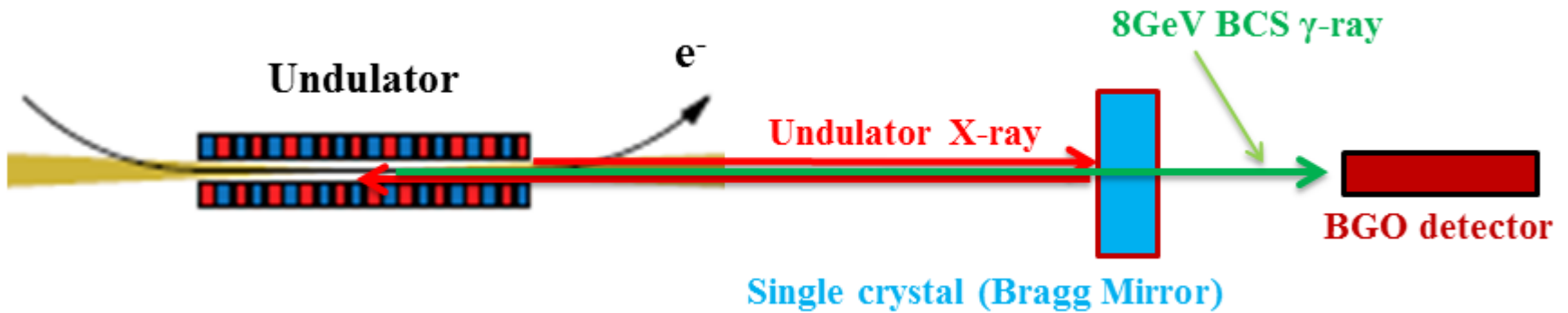


$\theta_x - \theta_y$  scan @ normal-incidence  
of **9.133 keV**

Photon energy of incident X-ray matched Bragg condition  
at the normal-incidence (left) and unmatched (right).

# Plan of Test Experiment for $\gamma$ -ray Production

## Schematic Drawing of $\gamma$ -ray Production System



### Multipole Wiggler

76mm  $\times$  51 periods

$K_{\max} = 5.8$

Photon Energy = 5 ~ 30keV



### Mirror Chamber

Mirror Cooling System

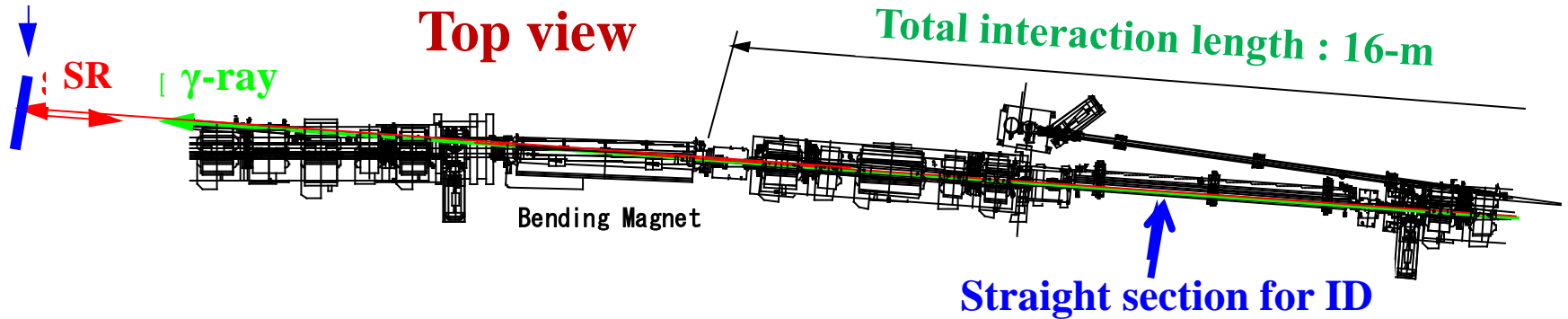
4-Axis Goniometer



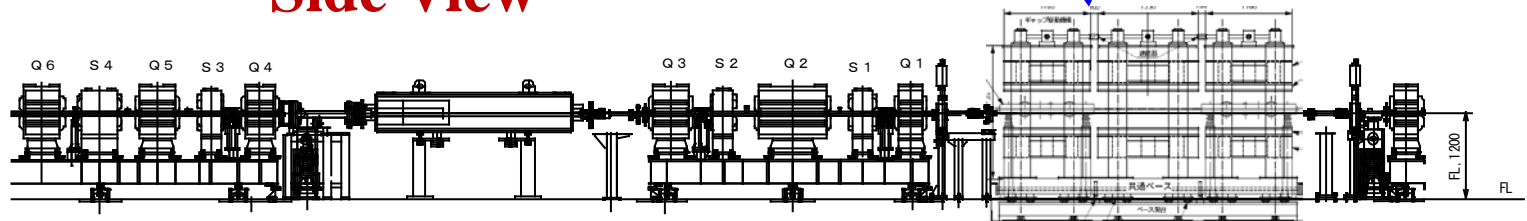
### $\gamma$ -ray Detector

# Plan of GeV Photons production at a beam diagnostics beamline, BL05SS

Single Crystal Mirror



**Side View**



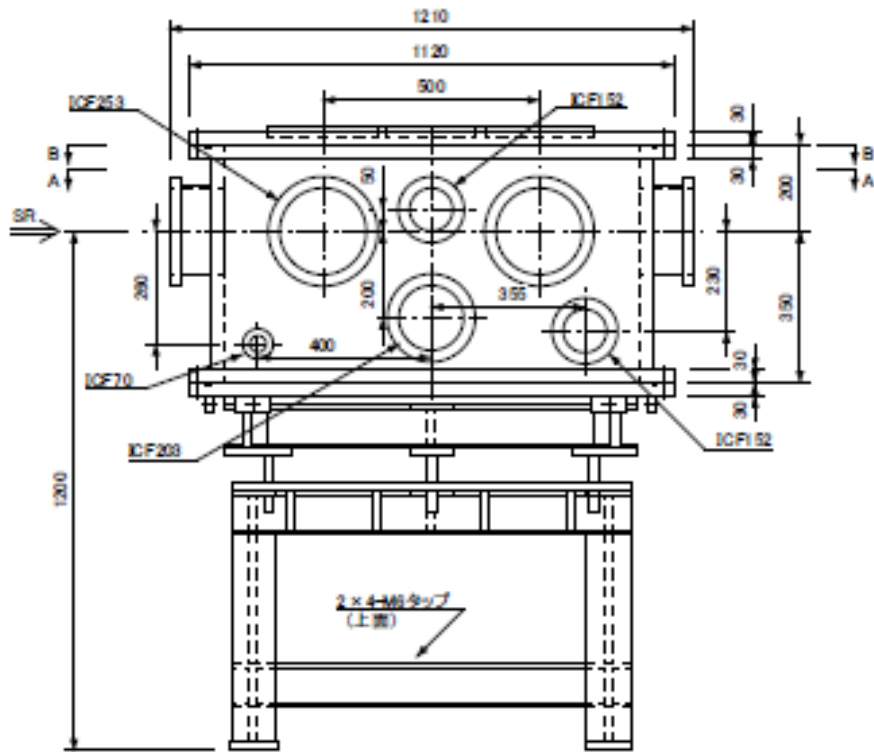
**Multipole Wiggler**

76mm  $\times$  51 periods

$K_{\max} = 5.8$

Photon Energy = 5 ~ 30keV

# Mirror Chamber

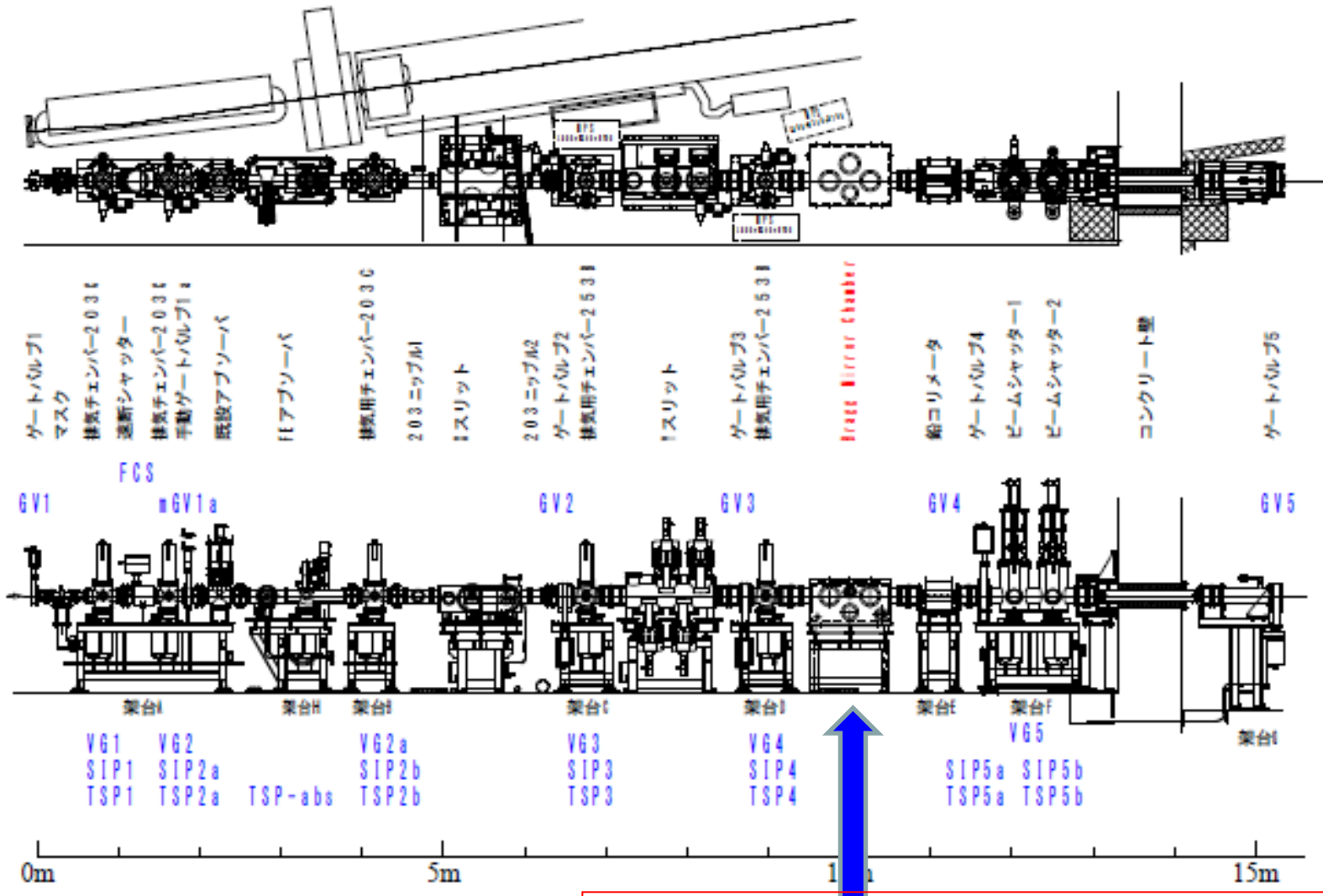


**Outer Dimension : 1120 mm × 820 mm × 610 mm**

**Mirror mounting system with cooling device  
4-Axis Goniometer  
(Focusing System)**



# Front-end of BL05SS at SPring-8



**Mirror Chamber (29m from ID center)**

# Summary

- We proposed backward Compton scattering using undulator radiation to reflect back by Bragg mirror.
- Preliminary reflectivity measurement of silicon single crystal.
- Experimental setup of  $\gamma$ -ray production by BCS using a single crystal (diamond) is now under preparation.

*Thank you for your attention*